

**MMBT4401** 

NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

### **Features**

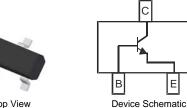
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (MMBT4403)
- Ideal for Medium Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

# **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound, • Note 3. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D •
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe • (Lead Free Plating) Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4

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Weight: 0.0082 grams (approximate)



Top View

#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                          | Symbol           | Value | Unit |
|---|------------------|-------|------|
| Collector-Base Voltage                  | V <sub>CBO</sub> | 60    | V    |
| Collector-Emitter Voltage               | V <sub>CEO</sub> | 40    | V    |
| Emitter-Base Voltage                    | V <sub>EBO</sub> | 6.0   | V    |
| Collector Current - Continuous (Note 1) | lc               | 600   | mA   |

## Thermal Characteristics

| Characteristic                                   | Symbol               | Value       | Unit |
|--|----------------------|-------------|------|
| Power Dissipation (Note 1)                       | PD                   | 300         | mW   |
| Thermal Resistance, Junction to Ambient (Note 1) | $R_{	heta JA}$       | 417         | °C/W |
| Operating and Storage Temperature Range          | TJ, T <sub>STG</sub> | -55 to +150 | °C   |

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which Notes: can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

No purposefully added lead. Halogen and Antimony Free. 2.

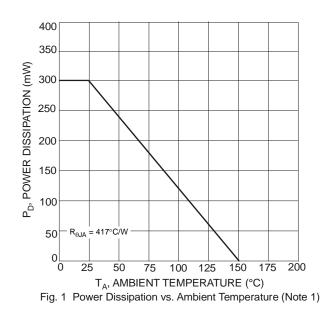
Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date 3 Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.

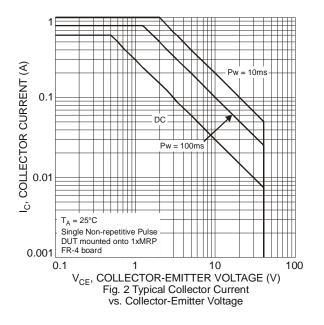


# **Electrical Characteristics** $@T_A = 25^{\circ}C$ unless otherwise specified

| Characteristic                       | Symbol               | Min                         | Max             | Unit   | Test Condition   |  |  |
|--------------------------------------|----------------------|-----------------------------|-----------------|--------|--|--|--|
| OFF CHARACTERISTICS (Note 4)         |                      |                             |                 |        | ÷  |  |  |
| Collector-Base Breakdown Voltage     | V <sub>(BR)CBO</sub> | 60                          | _               | V      | $I_{C} = 100 \mu A, I_{E} = 0$   |  |  |
| Collector-Emitter Breakdown Voltage  | V <sub>(BR)CEO</sub> | 40                          | —               | V      | $I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$  |  |  |
| Emitter-Base Breakdown Voltage       | V <sub>(BR)EBO</sub> | 6.0                         | —               | V      | $I_{E} = 100 \mu A, I_{C} = 0$   |  |  |
| Collector Cutoff Current             | ICEX                 | _                           | 100             | nA     | $V_{CE} = 35V, V_{EB(OFF)} = 0.4V$   |  |  |
| Base Cutoff Current                  | I <sub>BL</sub>      | _                           | 100             | nA     | $V_{CE} = 35V, V_{EB(OFF)} = 0.4V$   |  |  |
| ON CHARACTERISTICS (Note 4)          |                      |                             |                 |        | · · ·  |  |  |
| DC Current Gain                      | hre                  | 20<br>40<br>80<br>100<br>40 | <br><br>300<br> | _      | $\begin{split} & I_{C} = 100 \mu A, V_{CE} = 1.0 V \\ & I_{C} = 1.0 m A, V_{CE} = 1.0 V \\ & I_{C} = 10 m A, V_{CE} = 1.0 V \\ & I_{C} = 150 m A, V_{CE} = 1.0 V \\ & I_{C} = 500 m A, V_{CE} = 2.0 V \end{split}$ |  |  |
| Collector-Emitter Saturation Voltage | V <sub>CE(SAT)</sub> | —                           | 0.40<br>0.75    | V      | $I_{C} = 150 \text{mA}, I_{B} = 15 \text{mA}$<br>$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$   |  |  |
| Base-Emitter Saturation Voltage      | V <sub>BE(SAT)</sub> | T) 0.75 0.95 V<br>- 1.2 V   |                 | V      | $I_{C} = 150$ mA, $I_{B} = 15$ mA<br>$I_{C} = 500$ mA, $I_{B} = 50$ mA   |  |  |
| SMALL SIGNAL CHARACTERISTICS         |                      |                             |                 |        |  |  |  |
| Output Capacitance                   | C <sub>cb</sub>      | _                           | 6.5             | pF     | $V_{CB} = 5.0V, f = 1.0MHz, I_E = 0$   |  |  |
| Input Capacitance                    | Ceb                  |                             | 30              | pF     | $V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$   |  |  |
| Input Impedance                      | h <sub>ie</sub>      | 1.0                         | 15              | kΩ     |  |  |  |
| Voltage Feedback Ratio               | h <sub>re</sub>      | 0.1                         | 8.0             | x 10⁻⁴ | $V_{CE} = 10V, I_C = 1.0mA,$   |  |  |
| Small Signal Current Gain            | h <sub>fe</sub>      | 40                          | 500             | —      | f = 1.0 kHz  |  |  |
| Output Admittance                    | h <sub>oe</sub>      | 1.0                         | 30              | μS     |  |  |  |
| Current Gain-Bandwidth Product       | fT                   | 250                         | —               | MHz    | $V_{CE} = 10V$ , $I_C = 20mA$ ,<br>f = 100MHz  |  |  |
| SWITCHING CHARACTERISTICS            |                      |                             |                 |        |  |  |  |
| Delay Time                           | t <sub>d</sub>       | _                           | 15              | ns     | $V_{CC} = 30V, I_C = 150mA,$   |  |  |
| Rise Time                            | tr                   | _                           | 20              | ns     | $V_{BE(off)} = 2.0V, I_{B1} = 15mA$  |  |  |
| Storage Time                         | ts                   | _                           | 225             | ns     | $V_{CC} = 30V, I_C = 150mA,$   |  |  |
| Fall Time                            | t <sub>f</sub>       |                             | 30              | ns     | $I_{B1} = I_{B2} = 15 \text{mA}$   |  |  |

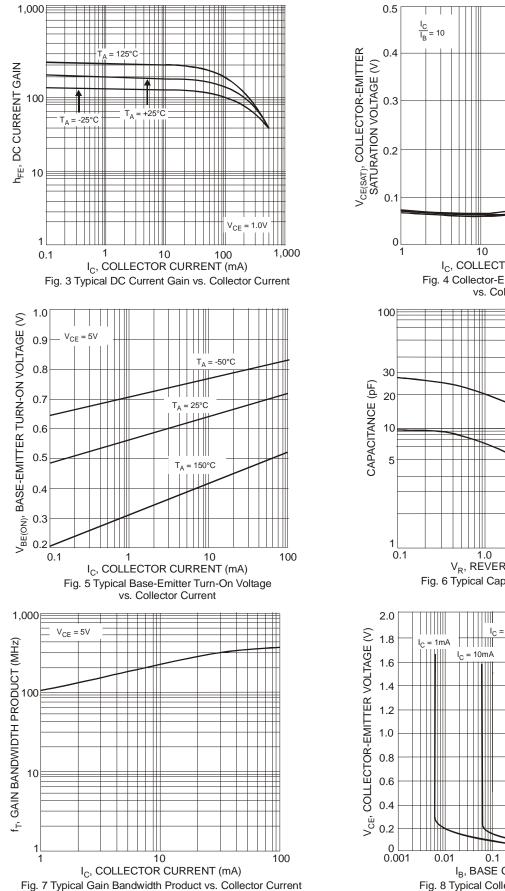
Notes: 4. Short duration pulse test used to minimize self-heating effect.

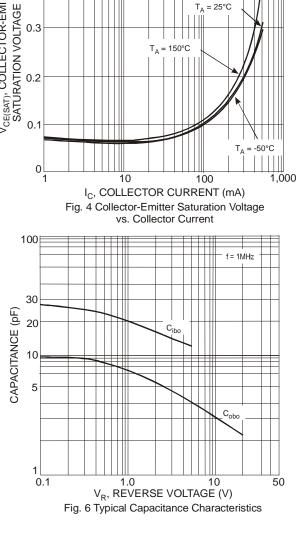


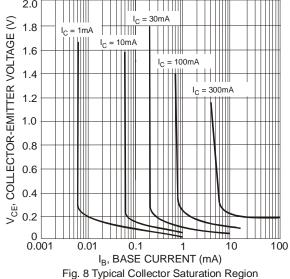




# **MMBT4401**









## Ordering Information (Note 5)

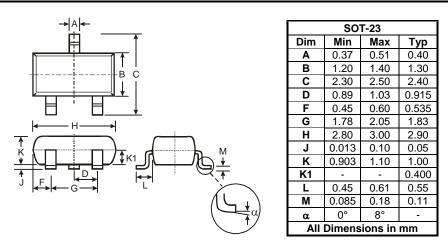
| Part Number   | Case   | Packaging          |
|---------------|--------|--------------------|
| MMBT4401-7-F  | SOT-23 | 3000/Tape & Reel   |
| MMBT4401-13-F | SOT-23 | 10,000/Tape & Reel |

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

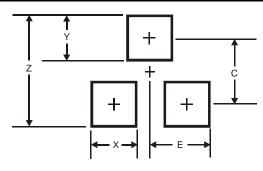
#### **Marking Information**

| Code J K L M N P R S T U V W X Y Z A B              | Date Code Ke | ₽V   |      |      |      |      | к<br>Ц | 2X   | ×    | ۲M =<br>۲ = ۲ | = Date C<br>/ear (ex | Code M<br>:: N = 2 | 0    | -    | 9    |      |      |      |      |
|---|--------------|------|------|------|------|------|--------|------|------|---------------|----------------------|--------------------|------|------|------|------|------|------|------|
|   | Year         | 1998 | 1999 | 2000 | 2001 | 2002 | 2003   | 2004 | 2005 | 2006          | 2007                 | 2008               | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 |
| Month Jan Feb Mar Apr May Jun Jul Aug Sep Oct Nov D | Code         | J    | K    | L    | М    | Ν    | Р      | R    | S    | Т             | U                    | V                  | W    | Х    | Y    | Z    | Α    | В    | С    |
|   | Month        | Jan  |      | Feb  | Mar  | r    | Apr    | May  | y    | Jun           | Jul                  |                    | Aug  | Sep  |      | Oct  | Nov  | 1    | Dec  |
| Code 1 2 3 4 5 6 7 8 9 O N                          | Code         | 1    |      | 2    | 3    |      | 4      | 5    |      | 6             | 7                    |                    | 8    | 9    |      | 0    | N    |      | D    |

# **Package Outline Dimensions**



# **Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.9           |
| Х          | 0.8           |
| Y          | 0.9           |
| С          | 2.0           |
| E          | 1.35          |

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